

# Photovoltaics

## LECTURE 9

- Diode summary
- photovoltaic effect
- the Sun as a resource
- absorption of photons
- generation of electron-hole pairs

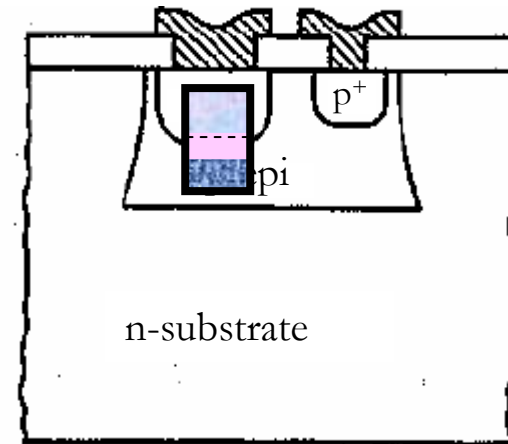
# Practical np-junction diodes and our model

Discrete diode: 200V, 70A

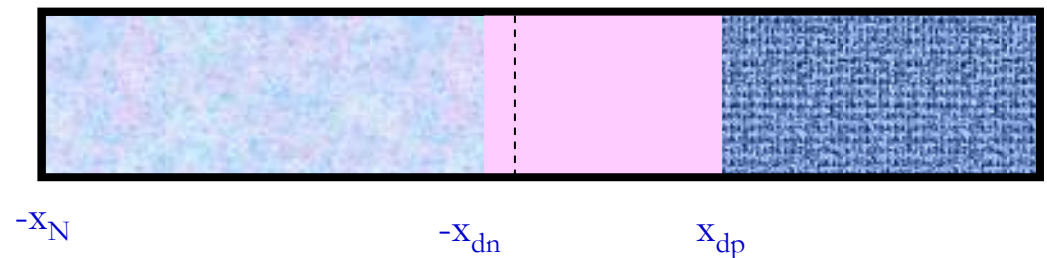


IC diode: 1V, 1mA

np diode with ohmic contact to p-region

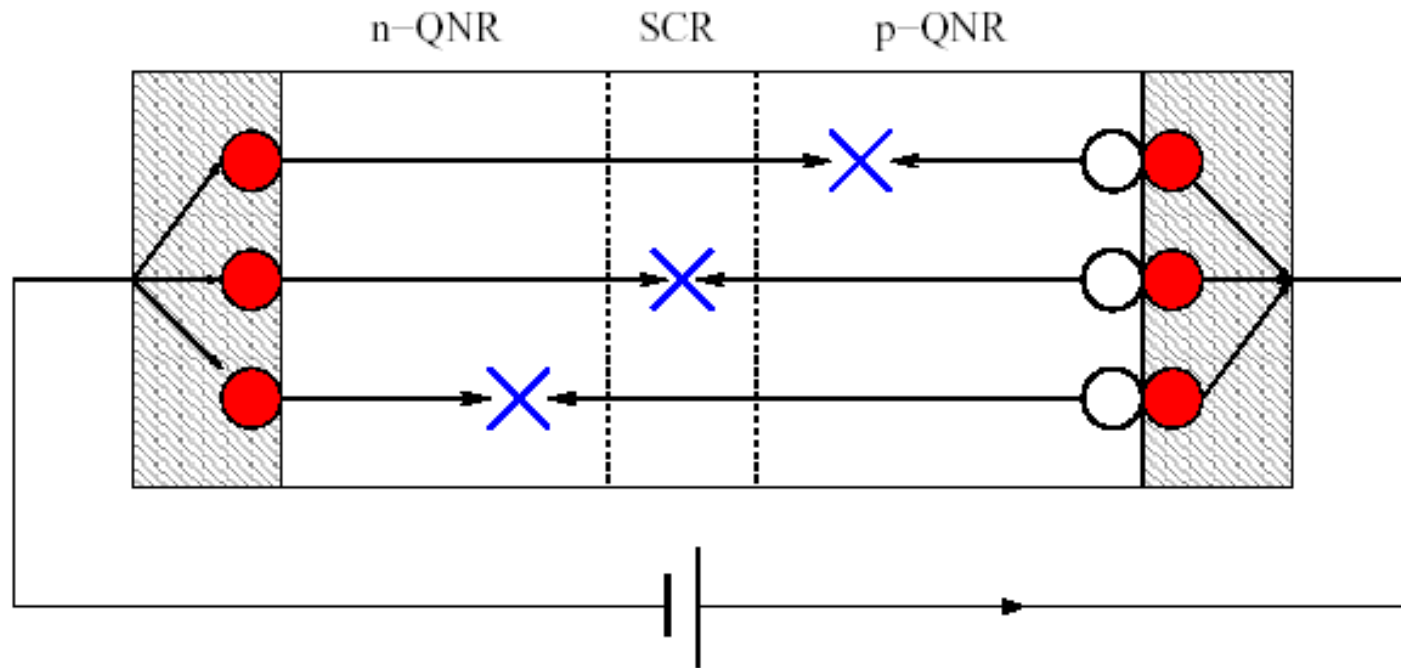


Our 1-D model



Sec. 6.6

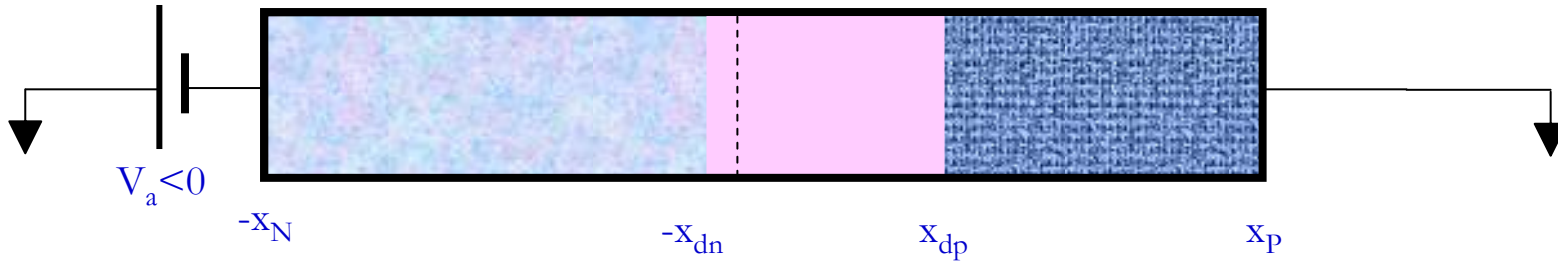
# Bipolar conduction



What is going on here?

## Sec. 6.6

## Diode calculations



$$\begin{aligned}
 -\nabla^2 \psi &= \frac{q}{\epsilon} [p - n + N_D - N_A] \\
 J_e &= -qn\mu_e \nabla \psi + qD_e \nabla n \\
 J_h &= -qp\mu_h \nabla \psi - qD_h \nabla p \\
 \frac{\partial n}{\partial t} &= \frac{1}{q} \nabla \cdot J_e - \frac{n - n_0}{\tau_e} \\
 \frac{\partial p}{\partial t} &= -\frac{1}{q} \nabla \cdot J_h - \frac{p - p_0}{\tau_h} .
 \end{aligned}$$

Pick a region, e.g., p-QNR for  $n$  and  $J_e$



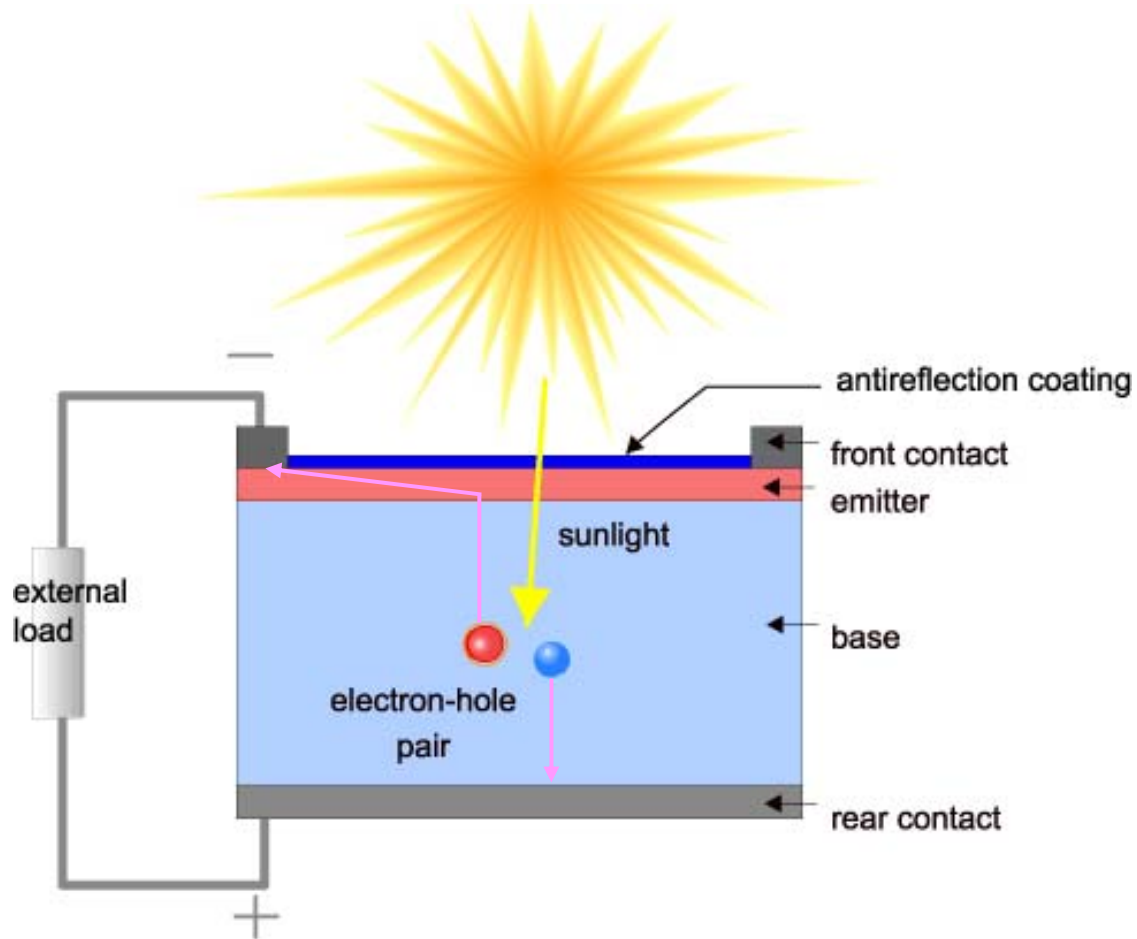
General solution:

$$n(x) - n_{0p} = Ae^{x/L_e} + Be^{-x/L_e}$$

Boundary conditions:

$$\begin{aligned}
 n(x_P) &\equiv n(\infty) = n_{0p} \quad \text{if contact is?} \\
 n(x_{dp}) &= n_{0p} e^{-V_a/V_{th}}
 \end{aligned}$$

# The Photovoltaic Effect



We need to consider:

- 1.
- 2.
- 3.
- 4.

# PV: large and small



12 MW Arnstein,  
Germany

90 MW Sarnia, Ontario

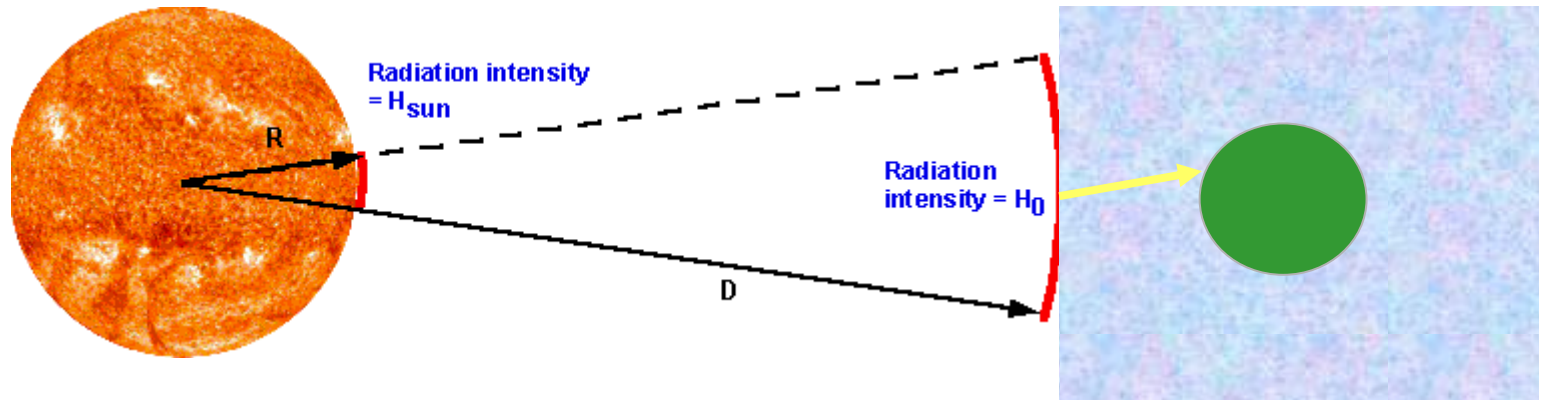
5kW Boston  
Massachusetts

<http://256.com/solar/>

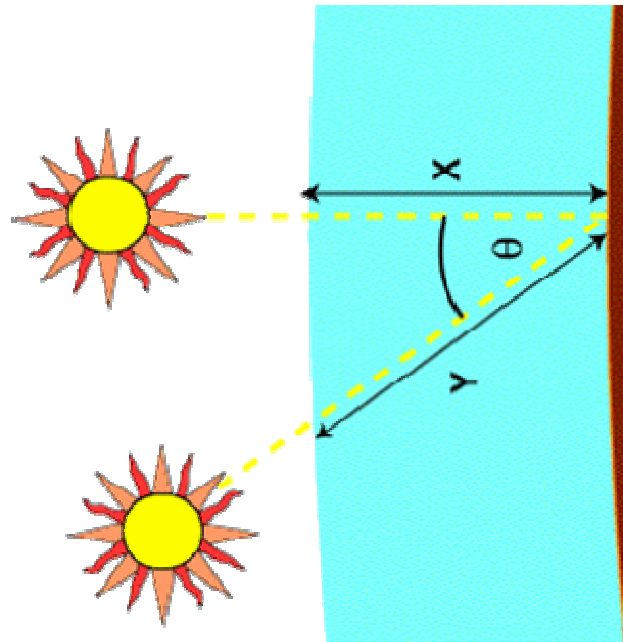


## Sec. 7.1

## The sun as a resource

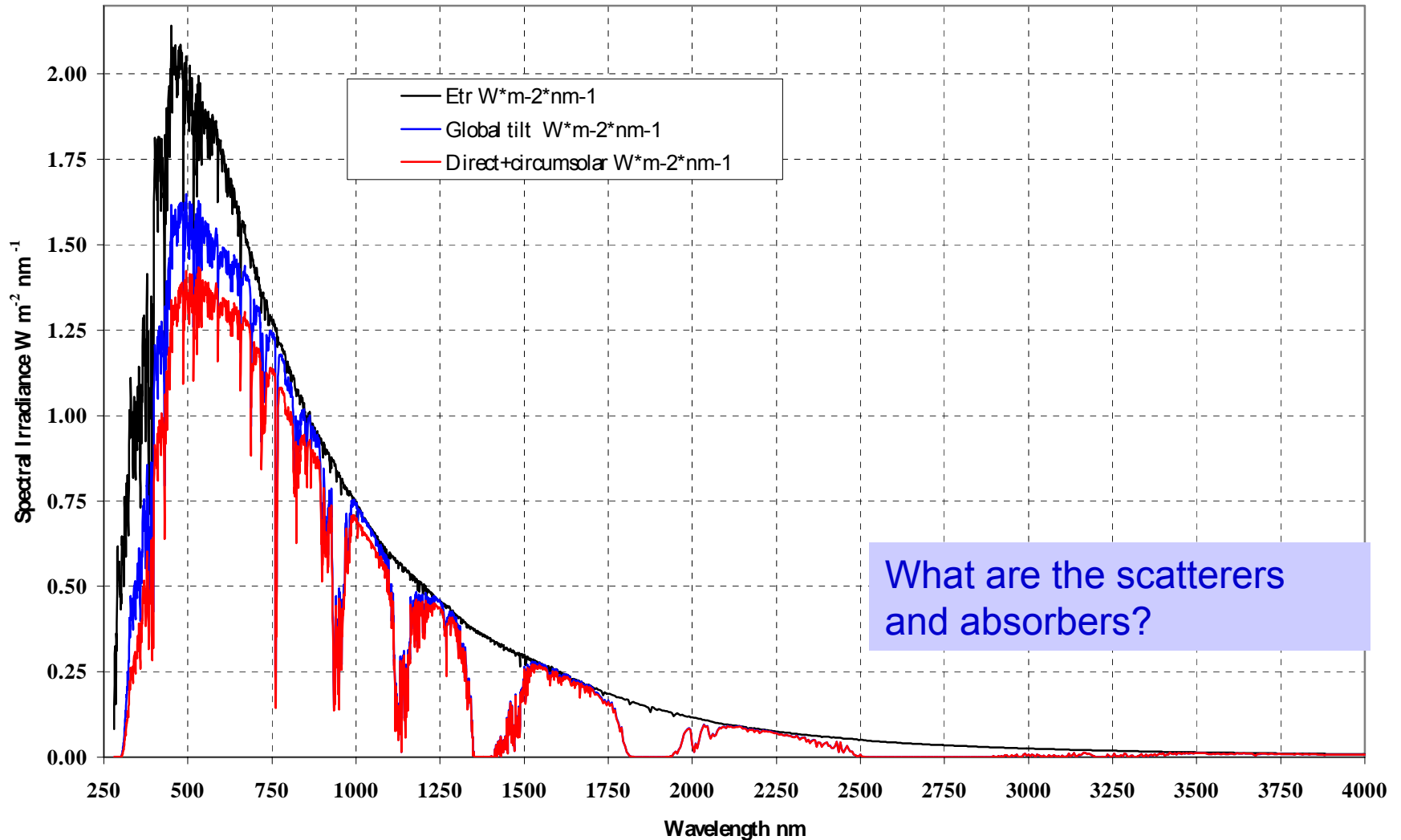


- Value for  $H_{\text{sun}}$  ?
- How is the energy generated ?
- Value for  $H_0$  ?
- How much is lost in the atmosphere ?
- What is Air Mass ?



# Irradiance standards

ASTM G173-03 Reference Spectra





## Sec. 7.2

## Absorption

TEM plane wave

$$\mathcal{E}_y(x) = \mathcal{E}_0 e^{ikx}$$

Refractive index

$$k = \frac{\omega}{c/n^*} = \frac{\omega(n_r + ik_r)}{c} \equiv \frac{2\pi(n_r + ik_r)}{\lambda}$$

$$\mathcal{E}_y(x) = \mathcal{E}_0 e^{i2\pi n_r x/\lambda} e^{-2\pi k_r x/\lambda}$$

What's this?

$$\vec{S} = \vec{\mathcal{E}} \times \vec{H}$$

What characterizes the attenuation?

$$S_x = \mathcal{E}_y H_z = \sqrt{\frac{\epsilon}{\mu}} |\mathcal{E}_y|^2 = \sqrt{\frac{\epsilon}{\mu}} \mathcal{E}_y(x) \mathcal{E}_y^*(x) = \sqrt{\frac{\epsilon}{\mu}} \mathcal{E}_0^2 e^{-\alpha x}$$

What's this?

$$\alpha = \square$$

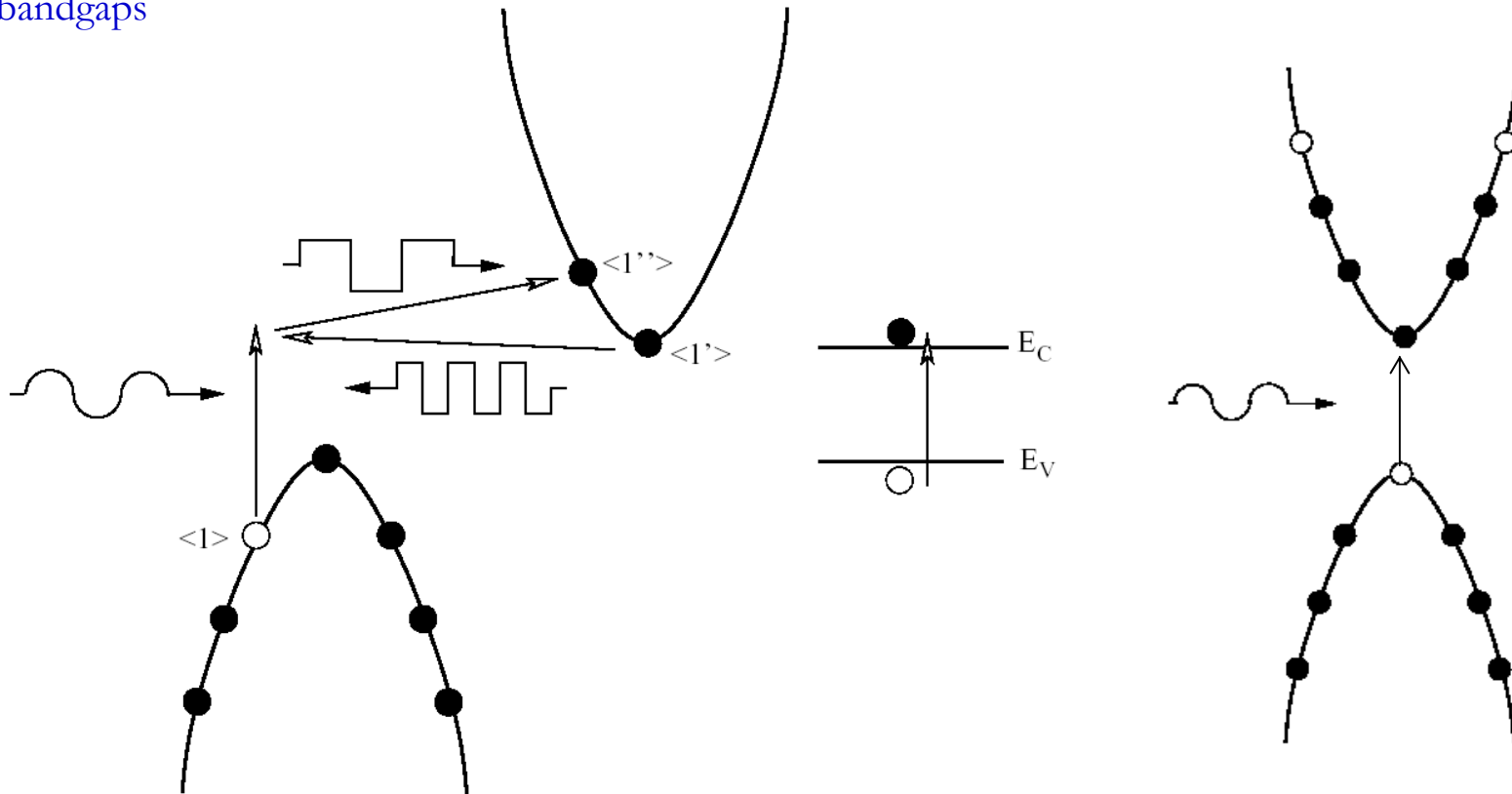
$$\equiv \square$$

## Sec. 7.3

## Photogeneration

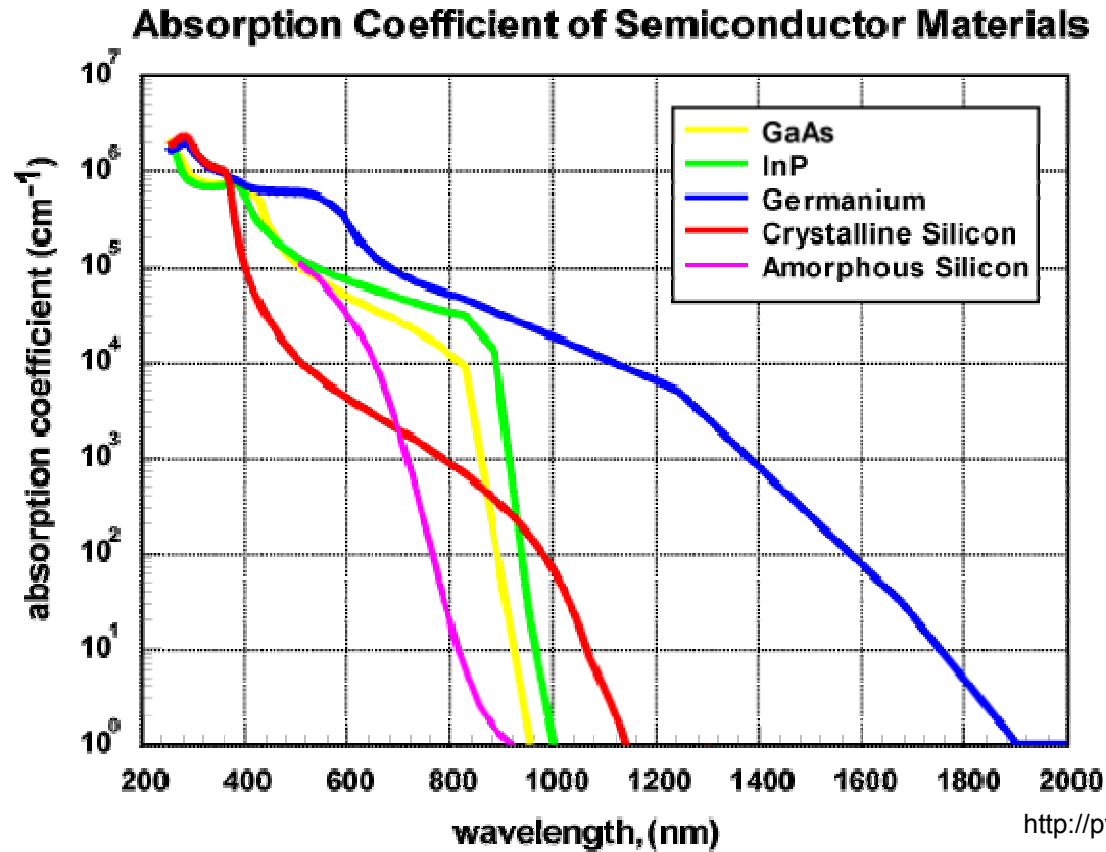
Consider materials with

bandgaps



Which material is likely to have the higher absorption coefficient?

# Absorption coefficient



What is the cut-off energy?

Which of these materials has a direct bandgap?

Secs.  
5.2.1, 7.3

## Derivation of Generation rate

$$\begin{aligned} -\nabla^2\psi &= \frac{q}{\epsilon}[p - n + N_D - N_A] \\ J_e &= -qn\mu_e\nabla\psi + qD_e\nabla n \\ J_h &= -qp\mu_h\nabla\psi - qD_h\nabla p \\ \frac{\partial n}{\partial t} &= \frac{1}{q}\nabla \cdot J_e - \frac{n - n_0}{\tau_e} \\ \frac{\partial p}{\partial t} &= -\frac{1}{q}\nabla \cdot J_h - \frac{p - p_0}{\tau_h} \end{aligned}$$

Let  $p$  be photon density  $P$  photons/ $m^3s$

Let  $J_h$  be photon flux  $F$  photons/ $m^2s$

Let  $U$  be generation of EHPs  $G_{op}$  EHPs/ $m^3s$

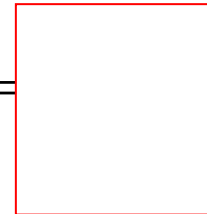
Write down the photon balance equation

$$\frac{\partial P(\lambda)}{\partial t} + \boxed{\phantom{000000}}$$

Express  $F$  in terms of  $S$

Define

$\Phi_0 =$



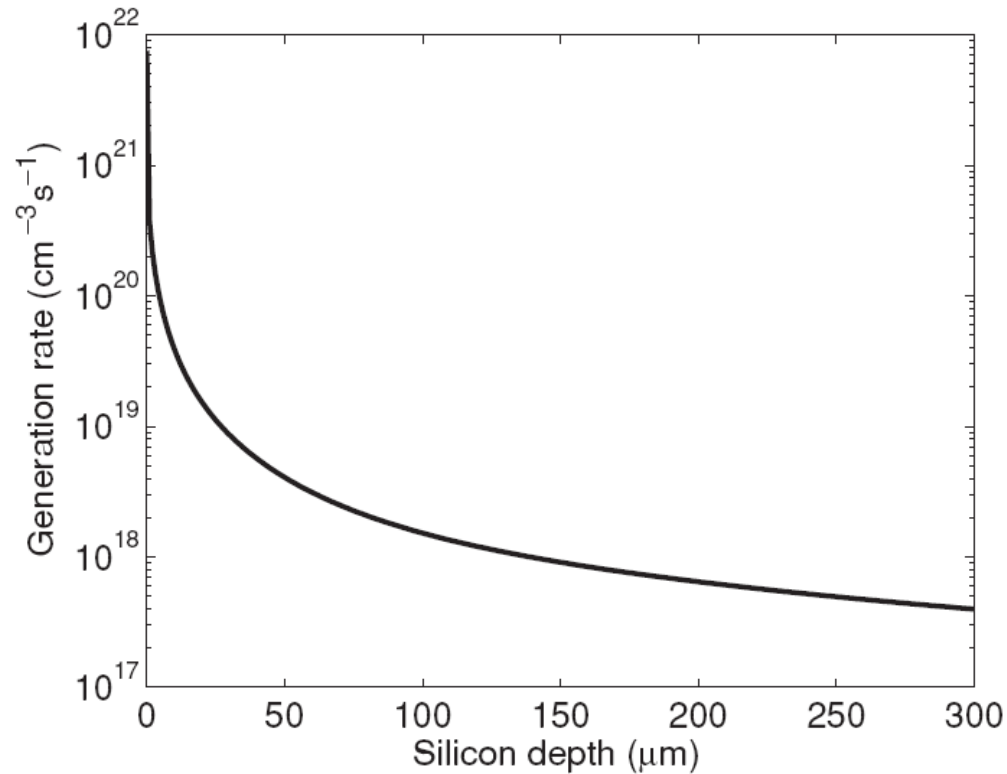
Solve for  $G_{op}$

$G_{op}(\lambda) =$



# The generation rate

$$G_{\text{op}}(\lambda) = \alpha(\lambda)\Phi_0(\lambda)e^{-\alpha x}$$

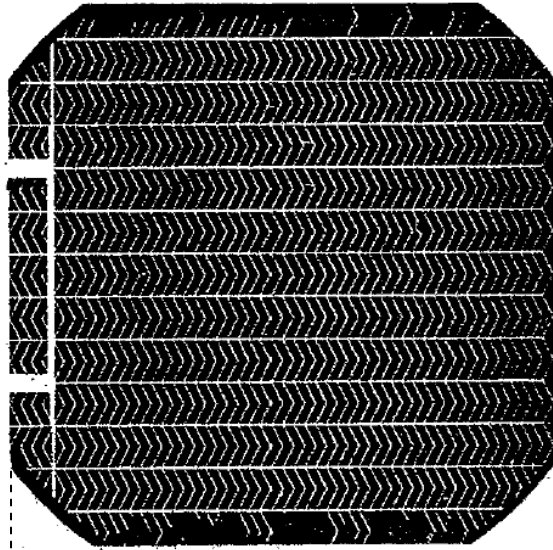


How does this curve help in the design of the solar cell?

Secs. 7.3,  
7.4

# Basic design issues resulting from $G_{op}(x)$

Plan view



Cross-section



- How deep should the junction be?
- Should the emitter be lightly or heavily doped?
- Should the emitter be  $n$ - or  $p$ -type?
- Should the base be thick or thin?
- Should the base be  $n$ - or  $p$ -type?